Medium Power Thyristors (Stud Version), 10 A

TO-208AA (TO-48)

FEATURES

- Improved glass passivation for high reliability and exceptional stability at high temperature
- High dI/dt and dV/dt capabilities
- Standard package
- Low thermal resistance
- Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- RoHS compliant
- Designed and qualified for industrial and consumer level

RoHS COMPLIANT

TYPICAL APPLICATIONS

- Medium power switching
- Phase control applications
- Can be supplied to meet stringent military, aerospace and other high reliability requirements

PRODUCT SUMMARY	
$I_{T(AV)}$	10 A

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		10	A
	T_C	85	°C
$I_{T(RMS)}$		25	A
I_{TSM}	50 Hz	225	A
	60 Hz	240	
I^2t	50 Hz	255	A^2s
	60 Hz	233	
V_{DRM}/V_{RRM}		100 to 1200	V
t_q	Typical	110	µs
T_J		- 65 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM}, MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE (1) V	V_{RSM}, MAXIMUM NON-REPETITIVE PEAK VOLTAGE (2) V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
10RIA	10	100	150	20
	20	200	300	10
	40	400	500	
	60	600	700	
	80	800	900	
	100	1000	1100	
	120	1200	1300	

Notes

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dI/dt does not exceed 20 A/µs

(2) For voltage pulses with $t_p \leq 5$ ms

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave			10	A
					85	°C
Maximum RMS on-state current	$I_{T(RMS)}$				25	A
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	225	A
		t = 8.3 ms			240	
		t = 10 ms	100 % V_{RRM} reapplied		190	
		t = 8.3 ms			200	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		255	A^2s
		t = 8.3 ms			233	
		t = 10 ms	100 % V_{RRM} reapplied		180	
		t = 8.3 ms			165	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied			2550	$A^2\sqrt{s}$
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			1.10	V
High level value of threshold voltage	$V_{T(TO)2}$	($I > \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			1.39	
Low level value of on-state slope resistance	r_{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			24.3	mΩ
High level value of on-state slope resistance	r_{t2}	($I > \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			16.7	
Maximum on-state voltage	V_{TM}	I_{pk} = 32 A, T_J = 25 °C, t_p = 10 ms sine pulse			1.75	V
Maximum holding current	I_H	T_J = 25 °C, anode supply 12 V resistive load			130	mA
Typical latching current	I_L				200	

SWITCHING					
PARAMETER		**SYMBOL**	**TEST CONDITIONS**	**VALUES**	**UNITS**
Maximum rate of rise of turned-on current	$V_{DRM} \leq 600$ V	dI/dt	$T_J = T_J$ maximum, V_{DM} = Rated V_{DRM} Gate pulse = 20 V, 15 Ω, t_p = 6 µs, t_r = 0.1 µs maximum I_{TM} = (2 x rated dI/dt) A	200	A/µs
	$V_{DRM} \leq 800$ V			180	
	$V_{DRM} \leq 1000$ V			160	
	$V_{DRM} \leq 1600$ V			150	
Typical turn-on time		t_{gt}	T_J = 25 °C, at rated V_{DRM}/V_{RRM}, T_J = 125 °C	0.9	µs
Typical reverse recovery time		t_{rr}	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, t_p > 200 µs, dI/dt = - 10 A/µs	4	
Typical turn-off time		t_q	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, t_p > 200 µs, V_R = 100 V, dI/dt = - 10 A/µs, dV/dt = 20 V/µs linear to 67 % V_{DRM}, gate bias 0 V to 100 W	110	

Note

- t_q = 10 µs up to 600 V, t_q = 30 µs up to 1600 V available on special request

BLOCKING				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**VALUES**	**UNITS**
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	100	V/µs
		$T_J = T_J$ maximum linear to 67 % rated V_{DRM}	300 (1)	

Note

(1) Available with: dV/dt = 1000 V/µs, to complete code add S90 i.e. 10RIA120S90

TRIGGERING					
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**VALUES**	**UNITS**
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum		8.0	W
Maximum average gate power	$P_{G(AV)}$			2.0	
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum		1.5	A
Maximum peak negative gate voltage	$-V_{GM}$	$T_J = T_J$ maximum		10	V
DC gate current required to trigger	I_{GT}	T_J = - 65 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	90	mA
		T_J = 25 °C		60	
		T_J = 125 °C		35	
DC gate voltage required to trigger	V_{GT}	T_J = - 65 °C		3.0	V
		T_J = 25 °C		2.0	
		T_J = 125 °C		1.0	
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum, V_{DRM} = Rated value		2.0	mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J$ maximum, V_{DRM} = Rated value	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**VALUES**		**UNITS**
Maximum operating junction and storage temperature range	T_J, T_{Stg}		- 65 to 125		°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.85		K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, flat and greased	0.35		
			TO NUT	**TO DEVICE**	
Mounting torque		Lubricated threads (Non-lubricated threads)	20 (27.5)	25	lbf · in
			0.23 (0.32)	0.29	kgf · m
			2.3 (3.1)	2.8	N · m
Approximate weight			14		g
			0.49		oz.
Case style		See dimensions - link at the end of datasheet	TO-208AA (TO-48)		

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	**SINUSOIDAL CONDUCTION**	**RECTANGULAR CONDUCTION**	**TEST CONDITIONS**	**UNITS**
180°	0.44	0.32	$T_J = T_J$ maximum	K/W
120°	0.53	0.56		
90°	0.68	0.75		
60°	1.01	1.05		
30°	1.71	1.73		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

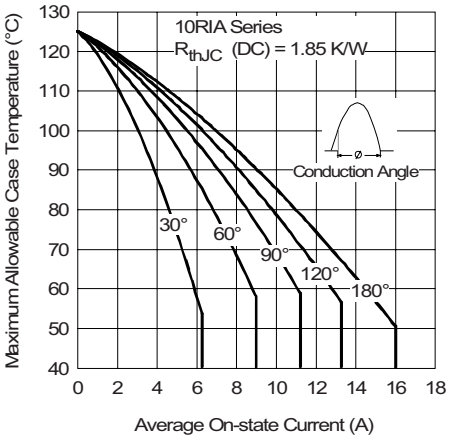

Fig. 1 - Current Ratings Characteristics

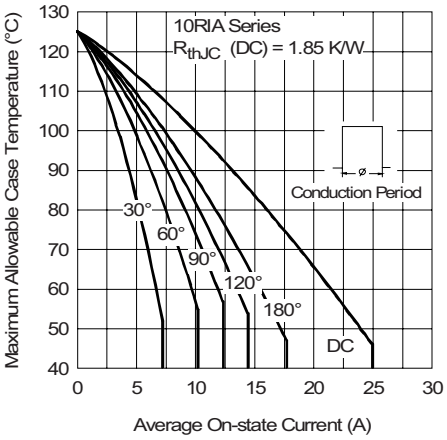

Fig. 2 - Current Ratings Characteristics

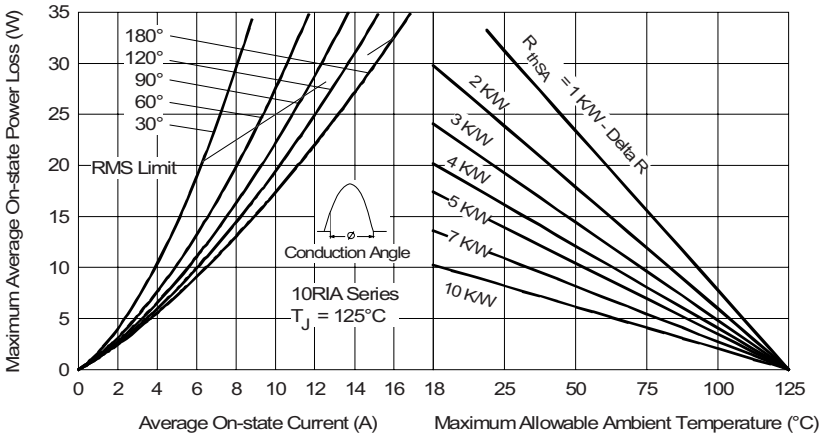

Fig. 3 - On-State Power Loss Characteristics

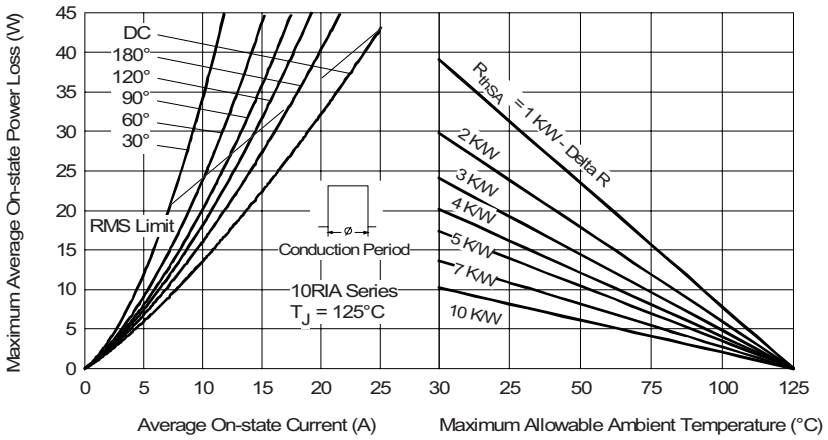

Fig. 4 - On-State Power Loss Characteristics

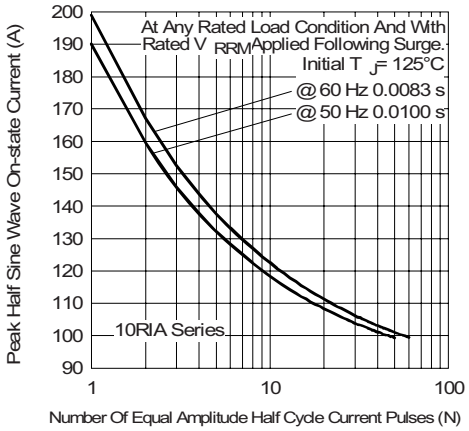

Fig. 5 - Maximum Non-Repetitive Surge Current

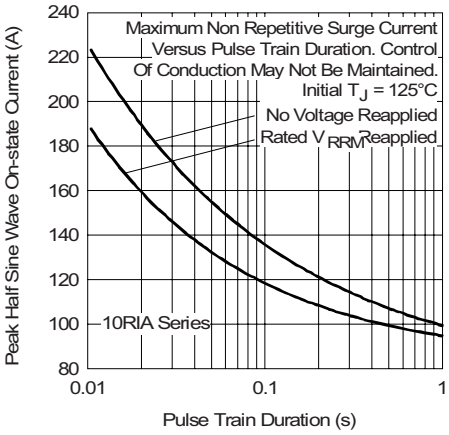

Fig. 6 - Maximum Non-Repetitive Surge Current

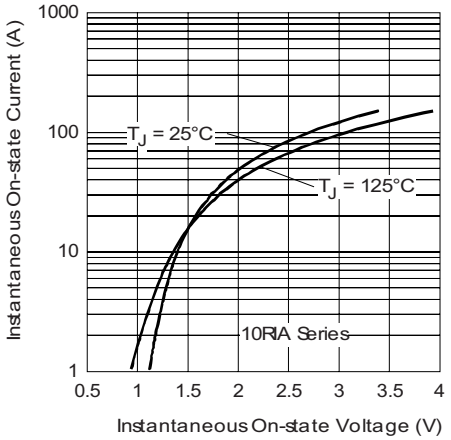

Fig. 7 - Forward Voltage Drop Characteristics

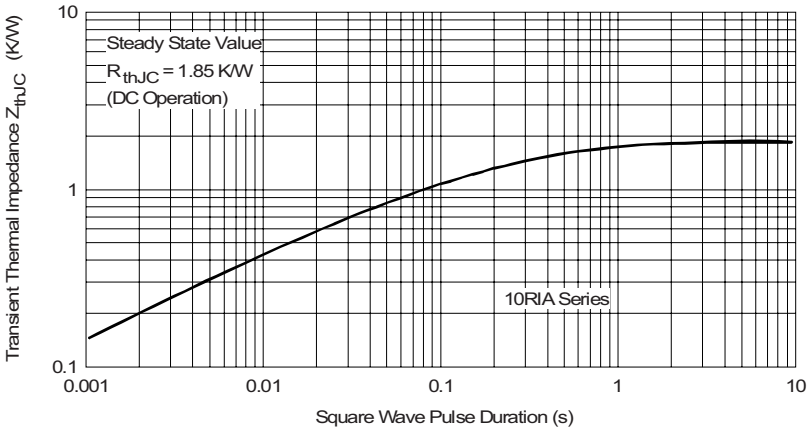

Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

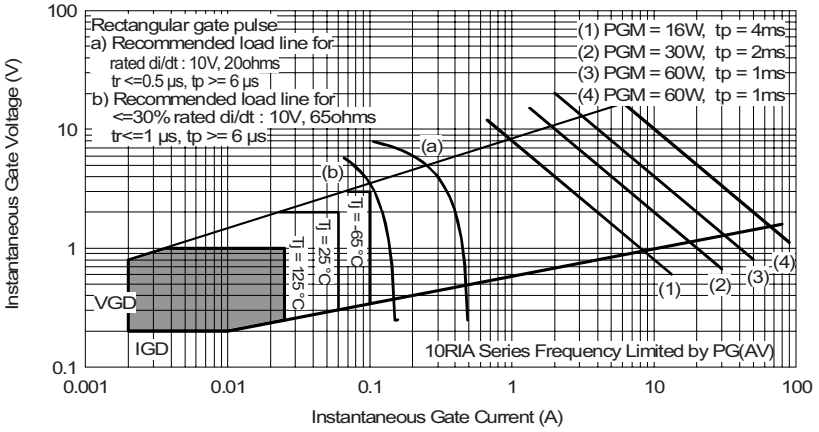

Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	10	RIA	120	M	S90
	1	2	3	4	5

1 - Current code

2 - Essential part number

3 - Voltage code x 10 = V_{RRM} (see Voltage Ratings table)

4 - None = Stud base TO-208AA (TO-48) 1/4" 28UNF-2A
M = Stud base TO-208AA (TO-48) M6 x 1

5 - Critical dV/dt:
None = 300 V/µs (standard value)
S90 = 1000 V/µs (special selection)

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95333

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- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

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